TO-92LM NPN Silicon NPN transistor in a TO-92LM Plastic Package.

KSA916

Complement to KSA916.

Audio power amplifier and driver stage amplifier applications.

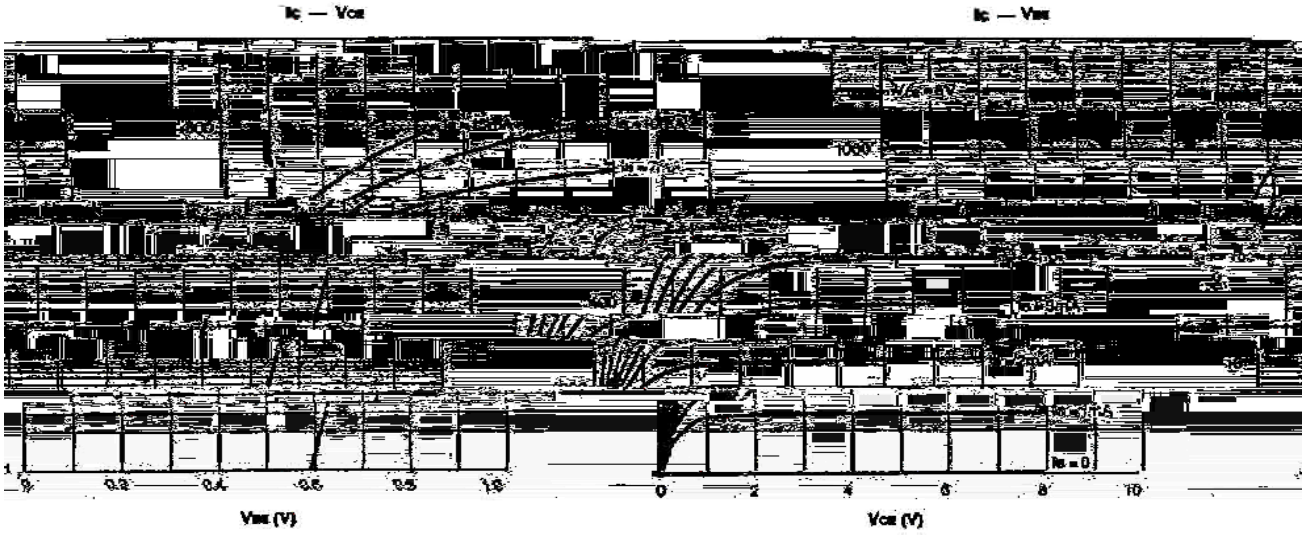
/ Absolute Maximum Ratings(Ta=25)

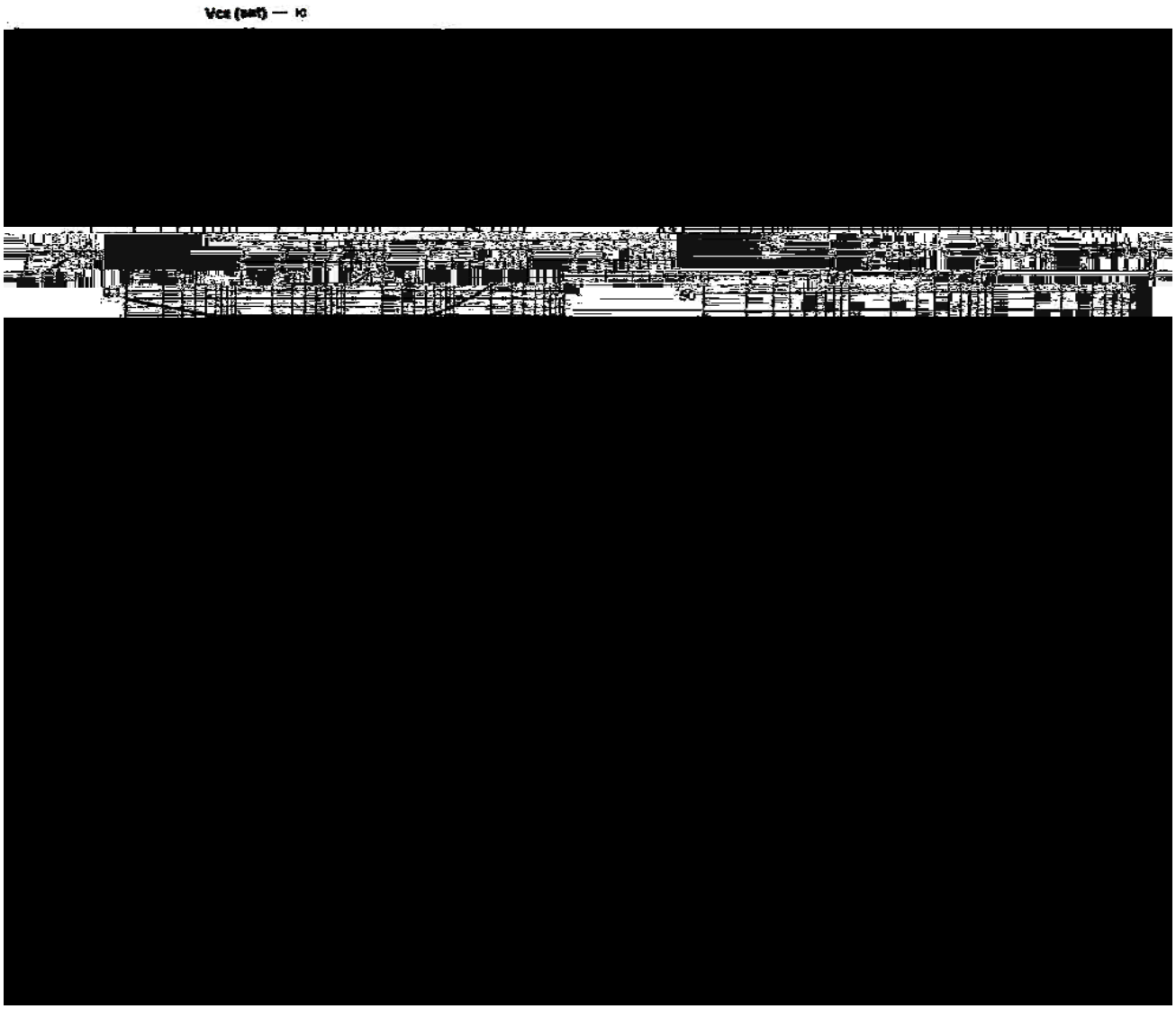
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	120	V
Collector to Emitter Voltage	V_{CEO}	120	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	800	mA
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=1.0mA I_E=0	120			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=10mA I_B=0	120			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-1.0mA I_C=0	5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=120V I_E=0			0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=5.0V I_C=100mA	80		240	
	$h_{FE(2)}$	V_{CE}=5.0V I_C=10mA	60			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA I_B=50mA			1.0	V
Transition Frequency	f_T	V_{CE}=5.0V I_C=100mA		120		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V I_E=0 f=1.0MHz			30	pF

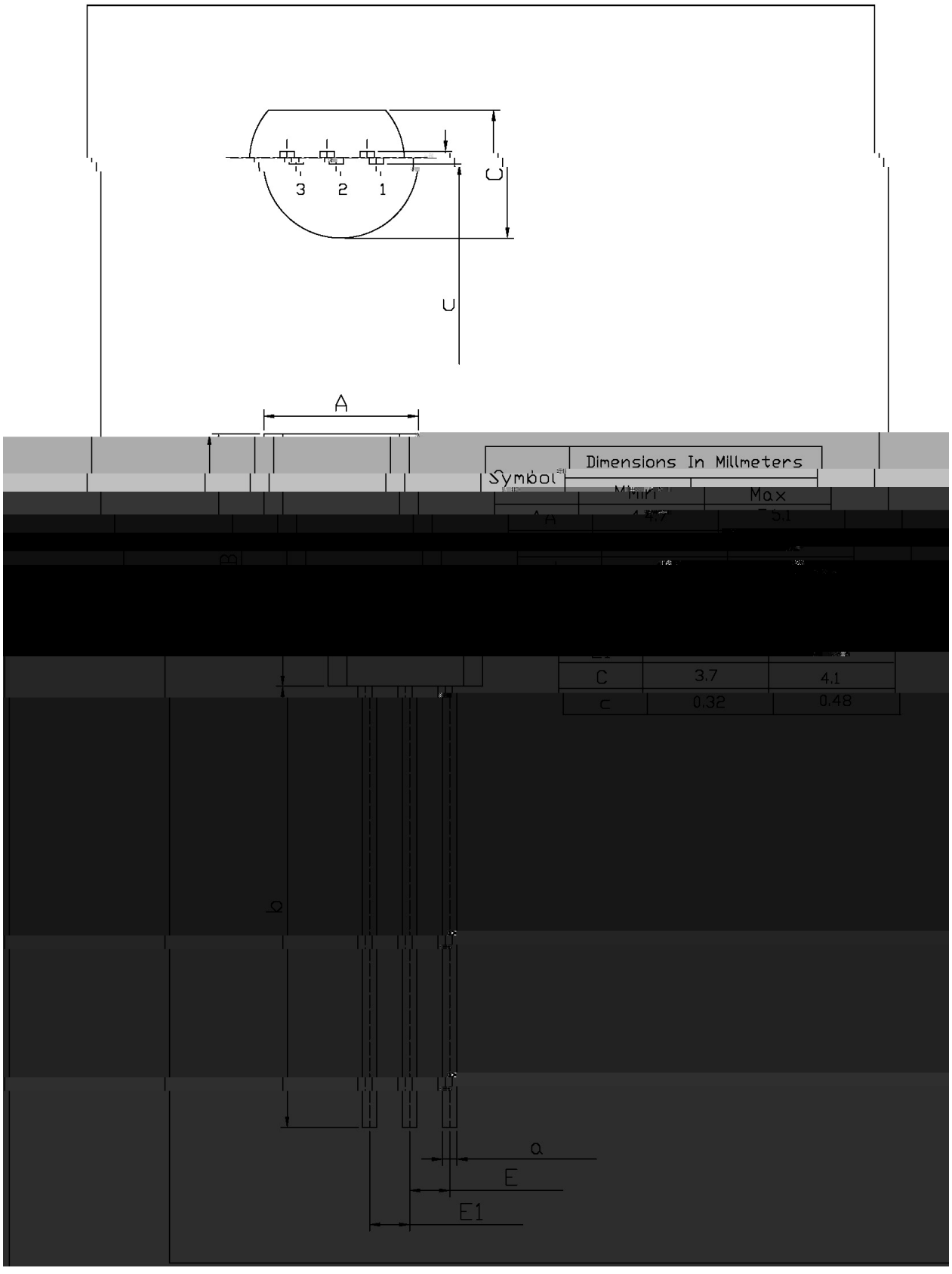
/ Electrical Characteristic Curve

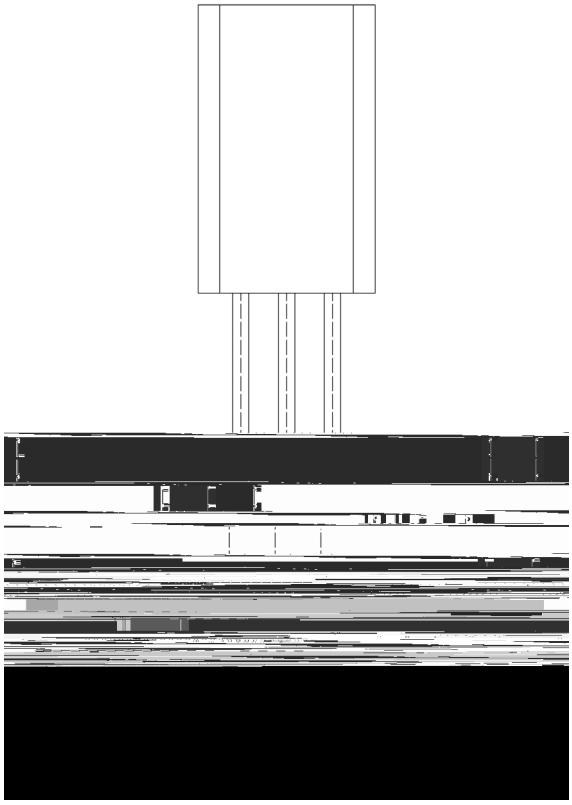




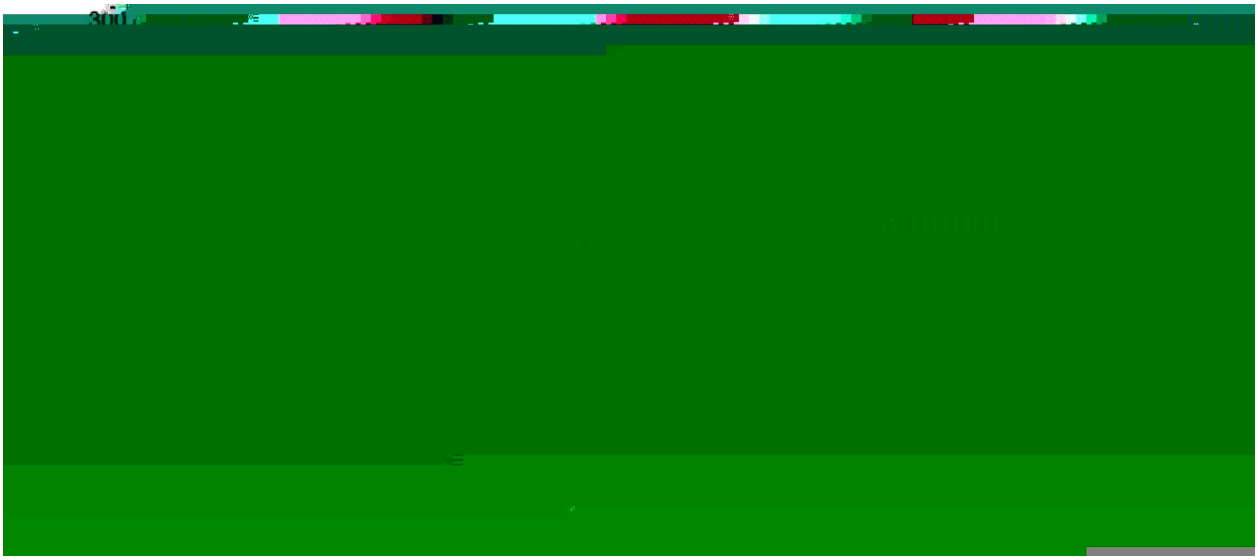
/ Package Dimensions

TO-92LM Unit: mm





( ) / Temperature Profile for Dip Soldering(Pb-Free)



						Note:	
1		25	150		60 90sec;	1.Preheating:25~150 , Time:60~90sec.	
2		255±5			5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.	
3				2 10 /sec.		3. Cooling Speed: 2~10 /sec.	

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units	Dimension	(unit mm3)